

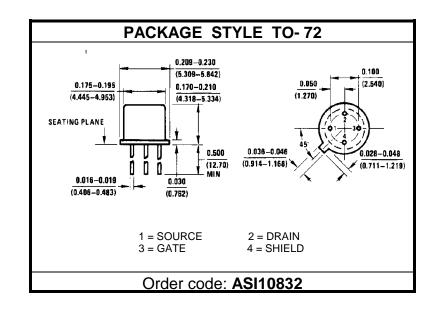
N-CHANNEL SILICON FET DEPLETION MODE

DESCRIPTION:

The **ASI BFW13** is Designed for Low Noise Video Amplifier Applications.

MAXIMUM RATINGS

I _D	10 mA					
I_{G}	5.0 mA					
V _{DS}	30 V					
V_{DG}	30 V					
V _{GS}	30 V					
P _{tot}	150 mW @ T _A = 110 ^O C					
TJ	-65 °C to +200 °C					
T _{STG}	-65 °C to +200 °C					
θ _{JA}	590 °C/W					



CHARACTERISTICS T_C = 25 °C

SYMBOL		TEST CONDIT	IONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I _{GS}	$V_{GS} = 10 \text{ V}$					100	рA
			$T_C = 150$ $^{\circ}C$			100	nA
I _{DSS}	$V_{DS} = 15 \text{ V}$	$V_{GS} = 0 V$		0.2		1.5	mA
V_{GS}	$V_{DS} = 15 \text{ V}$	$I_D = 50 \mu A$		0.1		1.0	٧
$V_{(P)GS}$	$V_{DS} = 15 \text{ V}$	$I_{D} = 500 \text{ pA}$				1.2	٧
ly _{fs} l	V _{DS} = 15 V	$V_{GS} = 0 \text{ V}$		1500			μS
ly _{os} l	VDS = 10 V	VGS = 0 V				10	F
ly _{fs} l	V _{DS} = 15 V	I _D = 200 μA	f = 1.0 MHz	500			μS
ly _{os} l	VDS = 13 V	10 = 200 μΑ	1 = 1.0 WH IZ			5.0	μ-0
C _{iss}	V _{DS} = 15 V		f = 1.0 MHz			5.0	рF
C_{rs}	V _{DS} = 13 V		1 – 1.0 IVII IZ			8.0	ρı
V_n	V _{DS} = 15 V	$I_D = 200 \mu A$	BW = 0.6 to 100 Hz			500	nV

ADVANCED SEMICONDUCTOR, INC.